

SNUBBERLESS TRIAC

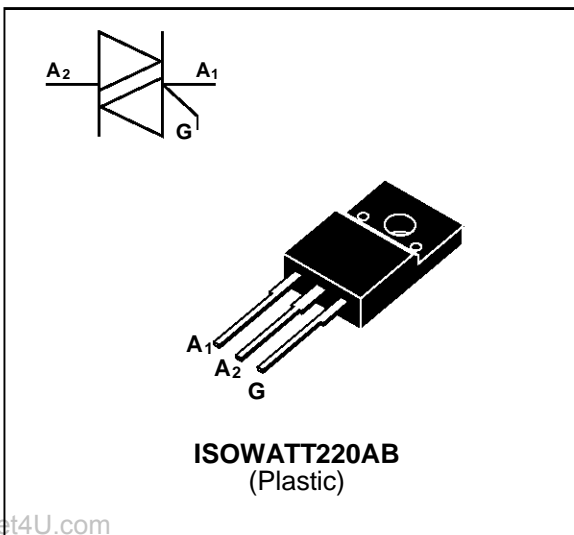
FEATURES

- $I_{T(RMS)} = 8\text{ A}$
- $V_{DRM} = V_{RRM} = 400\text{V to } 700\text{V}$
- EXCELLENT SWITCHING PERFORMANCES
- INSULATING VOLTAGE = $1500V_{(RMS)}$
- U.L. RECOGNIZED : E81734

DESCRIPTION

The T820/830W triacs use high performance glass passivated chip technology, housed in a fully molded plastic ISOWATT220AB package.

The SNUBBERLESS™ concept offers suppression of R-C network, and is suitable for applications such as phase control and static switch on inductive and resistive loads.



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ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	$T_c = 95^\circ\text{C}$	8	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$t_p = 16.7\text{ ms}$ (1 cycle, 60 Hz)	88	A
		$t_p = 10\text{ ms}$ (1/2 cycle, 50 Hz)	100	
I^2t	I^2t Value (half-cycle, 50 Hz)	$t_p = 10\text{ ms}$	50	A^2s
di/dt	Critical rate of rise of on-state current Gate supply : $I_G = 500\text{ mA}$ $dI_G/dt = 1\text{ A}/\mu\text{s}$.	Repetitive $F = 50\text{ Hz}$	20	$\text{A}/\mu\text{s}$
		Non Repetitive	100	
T_{stg} T_j	Storage temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 125	$^\circ\text{C}$
TI	Maximum lead temperature for soldering during 10s at 4.5 mm from case		260	$^\circ\text{C}$

Symbol	Parameter	T820 / 830-xxxW			Unit
		400	600	700	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ\text{C}$	400	600	700	V

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T820W / 830W**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	50	°C/W
Rth(j-c)	Junction to case for A.C (360° conduction angle)	3.1	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 1\text{ W}$ $P_{GM} = 10\text{ W}$ ($t_p = 20\ \mu\text{s}$) $I_{GM} = 4\text{ A}$ ($t_p = 20\ \mu\text{s}$)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Quadrant		T820	T830	Unit	
I_{GT}	$V_D = 12\text{V (DC)}$ $R_L = 33\ \Omega$	$T_j = 25^\circ\text{C}$	I-II-III	MAX	20	30	mA
V_{GT}	$V_D = 12\text{V (DC)}$ $R_L = 33\ \Omega$	$T_j = 25^\circ\text{C}$	I-II-III	MAX	1.5		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{k}\Omega$	$T_j = 125^\circ\text{C}$	I-II-III	MIN	0.2		V
tgt	$V_D = V_{DRM}$ $I_G = 500\text{mA}$ $di_G/dt = 3\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	I-II-III	TYP	2		μs
I_H^*	$I_T = 100\text{mA}$ Gate open	$T_j = 25^\circ\text{C}$		MAX	35	50	
V_{TM}^*	$I_{TM} = 11\text{A}$ $t_p = 380\ \mu\text{s}$	$T_j = 25^\circ\text{C}$		MAX	1.5		V
I_{DRM} I_{RRM}	VDRM rated VRRM rated	$T_j = 25^\circ\text{C}$		MAX	10		μA
		$T_j = 125^\circ\text{C}$		MAX	2		mA
dV/dt^*	Linear slope up to $V_D = 67\%V_{DRM}$ Gate open	$T_j = 125^\circ\text{C}$		MIN	200	300	$\text{V}/\mu\text{s}$
$(dV/dt)_c^*$	$(di/dt)_c = 4.5\text{ A/ms}$ (see note)	$T_j = 125^\circ\text{C}$		MIN	10	20	$\text{V}/\mu\text{s}$

* For either polarity of electrode A2 voltage with reference to electrode A1.

Note : In usual applications where $(di/dt)_c$ is below 4.5 A/ms, the $(dV/dt)_c$ is always lower than 10V/ μs , and, therefore, it is **unnecessary** to use a snubber R-C network across T820W / T830W triacs.

Fig.1 : Maximum power dissipation versus RMS on-state current.

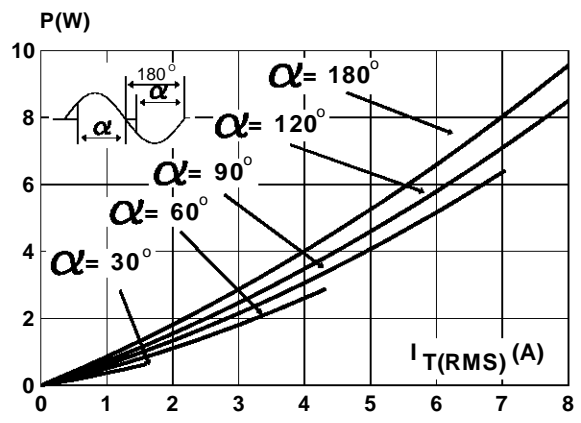


Fig.2 : Correlation between maximum power dissipation and maximum allowable temperature (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

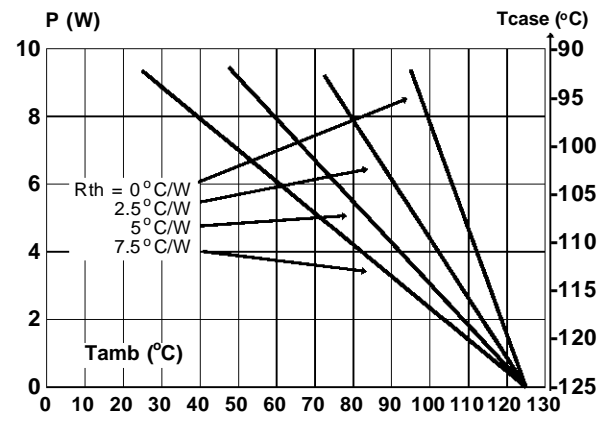


Fig.3 : RMS on-state current versus case temperature.

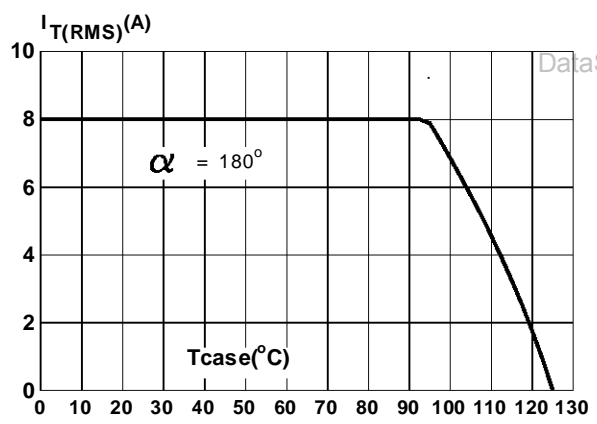


Fig.4 : Thermal transient impedance junction to case and junction to ambient versus pulse duration.

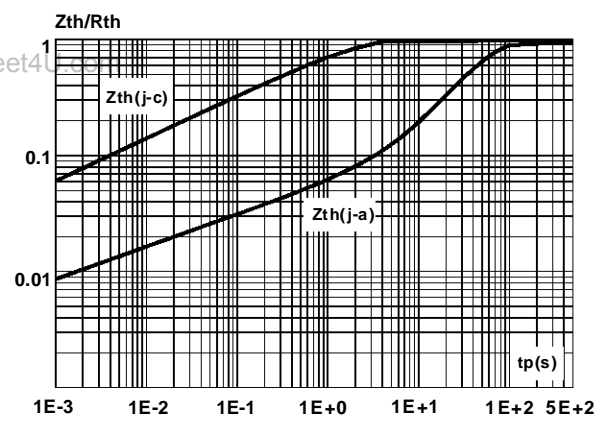


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

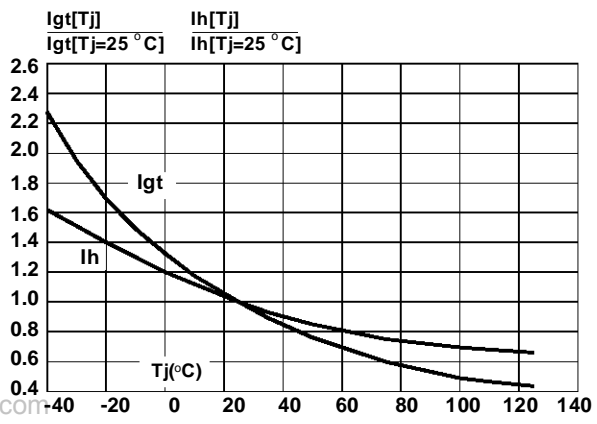
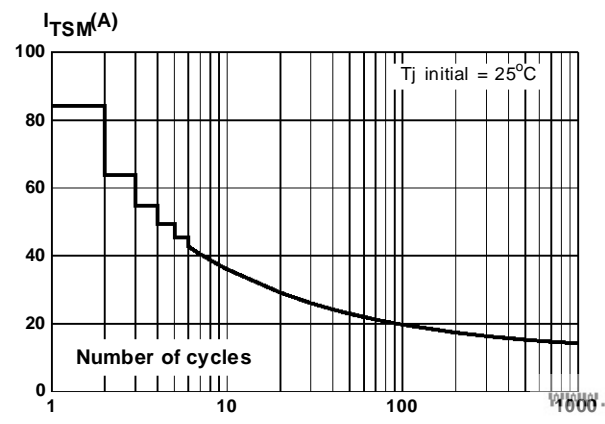


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.



T820W / 830W

Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10\text{ms}$, and corresponding value of I^2t .

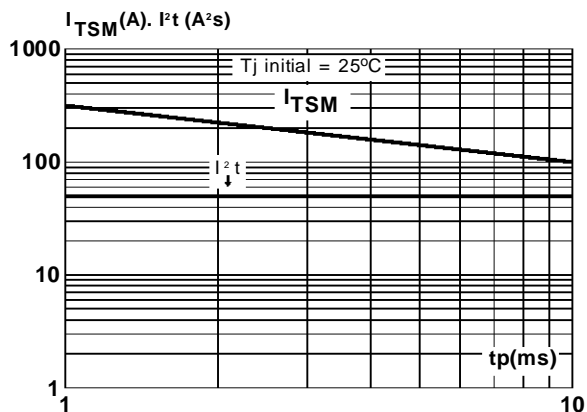
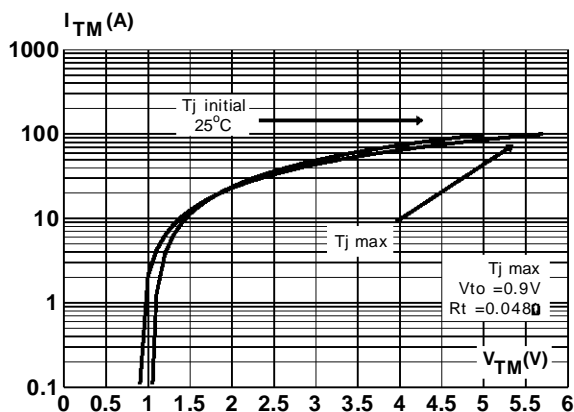


Fig.8 : On-state characteristics (maximum values).



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PACKAGE MECHANICAL DATA
 ISOWATT220AB

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	10	10.4	0.393	0.409
B	15.9	16.4	0.626	0.645
B1	9.8	10.6	0.385	0.417
C	28.6	30.6	1.126	1.204
D	16 typ		0.630 typ	
E	9	9.3	0.354	0.366
H	4.4	4.6	0.173	0.181
I	3	3.2	0.118	0.126
J	2.5	2.7	0.098	0.106
L	0.4	0.7	0.015	0.027
M	2.5	2.75	0.098	0.108
N	4.95	5.2	0.195	0.204
N1	2.4	2.7	0.094	0.106
O	1.15	1.7	0.045	0.067
P	0.75	1	0.030	0.039

Cooling method : C
 Marking : Type number
 Weight : 2.1g
 Recommended torque value : 0.55 m.N.
 Maximum torque value : 0.70 m.N.

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